Theory of param etric am pli cation in superlattices

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W e consider a high-frequency response of electrons in a single m in band of superlattice subject to dc and ac electric elds. W e show that Bragg re ections in m in band result in a param etric resonance which is detectable using ac probe eld. W e establish theoretical feasibility of phase-sensitive THz ampli cation at the resonance. The param etric ampli cation does not require operation in conditions of negative di erential conductance. This prevents a form ation of destructive dom ains of high electric eld inside the superlattice.

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M otion of an electronic wavepacket in a periodic lattice potential with a period a subject to a constant electric

eld Edc is characterized by oscillations of its velocity with the B loch frequency $!_{B} = eaE_{dc} = [1]$. B loch oscillations originate in Bragg re ections of the particle from the Brillouin zone boundary. Among solid state structures, arti cial sem iconductor superlattices (SLs) with a relatively large period and narrow bands are most suitable form an ifestation of B loch oscillations e ects 2]. In the stationary transport regime, B loch oscillations causes static negative di erential conductivity (NDC) of SL if $!_{\rm B} > 1$ (' 100 fs is a characteristic scattering time) [2]. For $!_{B} > 1$ and hom ogeneous distribution of electric eld inside SL, it can potentially provide a strong gain for THz frequencies [3]. However, in conditions of static NDC the same Bragg re ections, which give rise to B loch oscillations, do excite a soft dielectric relaxation mode resulting in a formation of domains of high eld inside SL [4]. The electric domains destroy Bloch gain in a long SL. Therefore an utilization of B loch gain is a di cult problem [5].

Using simple sem iclassical approach, let us consider now an in uence of Bragg re ections on dynamics of an electron subject to a strong ac (pump) eld $E_p(t) =$ $E_0 \cos!t$. Combining the acceleration theorem for the electron m om entum along the SL axis, $p = eE_p(t)$, and the tight-binding energy-m om entum dispersion for a single miniband of the width , "(p) = (=2) $\cos(pa=~)$, we arrive to the expression "(t) = $\begin{bmatrix} 1 \\ k=0 \end{bmatrix} C_{2k} \cos(2k!t)$, where $C_{2k} =$ J_{2k} (eaE $_0 = \sim !$) for k > 0 (J_n (x) are the Bessel functions). It shows that the electron energy within the miniband varies with frequencies which are som e even harmonics of $!: !_{"}^{even} = s!$ (s = 2;4;6:::). If a bias E_{dc} is also included to the pump eld, "(t) oscillates with two combinations of frequencies ! B leven $!_{"}^{odd}$, where $!_{"}^{odd} = s!$ with s = 1;3;5:...and !_B However, in the presence of collisions the oscillations with Bloch frequency decay, whereas energy oscillations with the frequencies in posed by ac eld survive. The effective electron m ass in the nonparabolic m iniband also varies periodically with the frequency of energy oscillations. Now let us suppose that additionally a weak ac

eld $E_{pr} = E_1 \cos(!_1 t + \cdot)$ is also applied. The frequency of this probe eld !1 is xed by an external circuit (resonant cavity). Since electron transport in the band depends on an instant value of the e ective electron mass, one should expect the parametric resonance for $!^{(s)} = 1!_1$ (1 is an integer and $!_{"}^{(s)}$ stands for either $!_{"}^{even}$ or $!_{"}^{odd}$). The most strong parametric resonance occurs when l = 2, that is for $! = 2 = !_1$ [6]. As in other param etric devices [6], the param etric resonance due to Bragg re ections can result in a regenerative ampli cation of the probe eld. How ever, currents at harm onics of the pump ac eld are generated in SL due to strong nonparabolicity of its miniband [7]. If the parametric ampli cation arises at the same frequencies as the frequencies of generated harm onics, the e ect of harm onics blurs out the weaker $(/ E_1)$ e ect of sm all-signal gain. This problem is well-known for the parametric ampli-

cation in Josephson junctions, which also have strong nonlinearity [8].

W e are interested in m anifestations of the param etric resonance due to B ragg re ections in the presence of collisions, i.e. in the miniband transport regime [5]. Here two main questions arise: Can the parametric resonance provide a high-frequency gain in the m iniband transport regime? Is it possible to avoid space-charge instability? Som e of these problem s have been discussed earlier. In 1977 Pavlovich rst used Boltzm ann transport approach to calculate the coe cient of intraband absorption of a weak probe eld $(!_1)$ in SL subjected to a strong ac pum p of com m ensurate frequency (!) [9]. He brie y m entioned a possibility of negative absorption for some $!_1 = !$. How ever, neither physical origin of the e ect nor its com patibility with conditions of electric stability were addressed in this pioneer work. Further, in a recent letter [10], we presented num erical support for a possibility of param etric ampli cation without form ation of electric dom ains in the miniband transport regime. Solving num erically balance equations for SL [11] we dem onstrated a feasibility of gain at even harm onics. In this situation, we observed that gain can exist in the absence of NDC. It guarantees electric stability for moderate concentrations of electrons [12].



FIG.1: (color online) Two schemes of the parametric ampli cation in superlattice without corruption from generated harmonics. In the presence of ac pump (red online) of the frequency !, parametric gain for a weak signal (green online) of the frequency !_1 arises either at !_1 = : !=2;3!=2;::: in biased SL (E dc \in 0) or at !_1 = : 2!;4!;::: in unbiased SL (E dc = 0).

In this paper, we analytically calculate gain of a weak high-frequency (THz) probe eld in SL m in iband under the conditions of parametric resonance, $!_{"}^{(s)}=2$ = $!_{1}$, caused by the action of a strong ac pumpeld. The physical origin of the parametric resonance is a periodic variation of e ective electron m asses in m in iband and, at high THz frequencies, also a variation of speci c quantum inductance. We prove that for a proper choice of relative phase a power is always transferred from the pump to the probe eld. Furtherm ore, we show that the same pump eld also modi es free carrier absorption in SL.We nd that the gain caused by the parametric resonance can su ciently overcom e the modi ed free carrier absorption and simultaneously remain una ected by the generated harm onics of the pump only in two distinct cases: For ampli cation at half-harm onics in biased SL and for ampli cation at even harm onics in unbiased SL (Fig. 1). In both these cases we predict a signi cant am pli cation at room temperature in the absence of NDC.

W ithin the sem iclassical approach [5] we rst solved Boltzm ann transport equation for a single m iniband and bichrom atic eld $E_p(t) + E_{pr}(t)$ with commensurate frequencies. Then we calculated the phase-dependent absorption of the probe eld, which is de ned as

$$A = hV(t) \cos(!_1 t +)i_t;$$
 (1)

where V (t) = \overline{V} (t)=V_p is the electron velocity (2" (p)=0p averaged over a distribution function satisfying the Boltzm ann equation and h:: i_t m eans averaging over a time period which is common for both pump (!) and probe (!₁)

elds. G ain corresponds to A < 0. Note that through the paper the averaged velocity V, averaged energy W = "=j"_{eq} jand eld strengths $E_{0;1}$ and E_{dc} are scaled to the E saki-T su peak velocity $V_p = (a=4\sim)$ (T), the equilibrium energy in absence of elds "_{eq} = (=2) (T) §] and the critical eld $E_c = \sim$ =ea 2, respectively. The tem perature factor is (T) = I_1 (=2 k_B T)= I_0 (=2 k_B T) (here $I_{0;1}$ (x) are the modi ed Bessel functions) [3]. Ab-

somption of a weak (E₁ ! 0) probe eld in SL (Eq.1) is linear in E₁. It can be naturally represented as the sum of phase-dependent coherent and phase-independent incoherent components $A = A_{coh} + A_{inc}$.

Param etric e ects in the absorption are described by its coherent component. It has the form

$$A_{coh} = (_1=4) B \cos[2(_{opt})];$$
 (2)

where the am plitude of coherent absorption B > 0 and $_1 = E_1 = (!_1)$. The coherent component always provides gain if j $_{opt}$ j< =4. G ain has maximum at an optimalphase $_{opt}$. Under the action of pump eld, such energy storage parameters of SL as the energy of electrons in miniband W and mesoscopic electric reactance, which is described by the reactive current I^{sin} / V^{sin}, are simultaneously harmonically modulated. The variables B and $_{opt}$ can be represented in terms of the speci c harmonics of W (t) and out-of-phase component of electron velocity V^{sin} (t) as

$$B = B_{lf}^{2} + B_{hf}^{2}^{1=2}; \quad \tan(2_{opt}) = B_{hf} = B_{lf}; \quad (3)$$

$$B_{lf} = 2W_{s}^{sin} (!_{B});$$

$$B_{hf} = W_{s}^{cos} (!_{B} + !_{1}) \quad 2W_{s}^{cos} (!_{B}) + W_{s}^{cos} (!_{B} \quad !_{1})$$

$$V_{s}^{sin} (!_{B} + !_{1}) \quad V_{s}^{sin} (!_{B} \quad !_{1}); \quad (4)$$

where the index s is the sam e as involved in the condition of parametric resonance and the Fourier components of the quantum reactive parameters are given by

$$W_{k}^{cos} = \begin{array}{c} X \\ J_{1}() [J_{1 k}() + J_{l+k}()]K(!_{B} + l!); \\ V_{k}^{sin} = \begin{array}{c} X \\ J_{1}() [J_{l+k}() - J_{k}()]K(!_{B} + l!); \\ \end{bmatrix} \\ W_{k}^{sin} = \begin{array}{c} 1 \\ J_{1}() [J_{1 k}() - J_{k+k}()]V^{ET}(!_{B} + l!); \\ \end{bmatrix}$$

In Eqs. 5 = $E_0 = (!)$, the Esaki-T su drift velocity $V^{ET}(!_B) = \frac{!_B}{1 + (!_B)^2}$ [2, 5] and Esaki-T su energy K $(!_B) = \frac{1}{1 + (!_B)^2}$ [5, 11] determ ine the dependence of $W_k^{cos}(!_B)$, $W_k^{sin}(!_B)$ and $V_k^{sin}(!_B)$ on the dc bias E_{dc} . It worth to notice that instead of harm onics of energy we alternatively can consider harm onics of e ective electron m ass because m⁻¹ (**m**) / W.

In the low frequency range ! ;!₁ 1, we found that $B_{\rm hf}$! 0 and therefore $B = B_{\rm lf}$, while for THz frequencies (! & 1) both term $sB_{\rm lf}$ and $B_{\rm hf}$ contribute to B. The behavior of the absorbtion am plitude B at THz frequencies has two peculiarities. First, in uence of the out-of-phase component of electron velocity at the pump frequency and its harm onics also becomes important. As follows from Eq. (5), it describes inductive response of inertialm iniband electrons to ac eld in the limit ! 1: $V_1^{\rm sin} = E_0 = !$ L, L¹ = 2J₀()J₁() ¹K(!_B) [14].

Second, interaction of m iniband electrons with THz elds has quantum nature [5]. Therefore, even a very weak probe eld produces a back action on the SL reactive parameters. This is indicated by an appearance of virtual processes of absorption and em ission of one quantum of the probe eld (~1) in the expression for B_{hf} (Eq. (4)). In particular, B_{hf} is determined by the difference between changes in electron energy at absorption $W(!_B + !_1) W(!_B)$ and em ission $W(!_B) W(!_B !_1)$. The asymmetry in the elementary acts of em ission and absorption is caused by scattering. It resembles corresponding asymmetry revealed in the quantum description of THz B loch gain in dc biased SLs [15].

W e turn now to the analysis of the incoherent component of absorption A_{inc} , which is independent on both the ratio $!_1=!$ and phase di erence . It can be represented as

$$A_{inc} = \frac{1}{2} [V_{dc} (!_{B} + !_{1}) \quad V_{dc} (!_{B} \quad !_{1})]; \quad (6)$$

where $V_{dc} = hV i_t$ is the drift velocity induced in SL by the pump eld alone. It is determined by the well-known form ula [16]

$$V_{dc}(!_{B}) = \int_{1}^{X} J_{1}^{2}() V^{ET}(!_{B} + 1!):$$
(7)

A $_{\rm inc}$ describes the free carrier absorption m odi ed by the pump. Naturally, A $_{\rm inc}$ become as the usual free carrier absorption A $_{\rm inc}$ / $(1+ !_1^{\ 2} \ ^2)^{\ 1}$ in the absence of pump eld (E $_0$ = E $_{\rm dc}$ = 0). Remarkably, as follows from Eq. (6), the pump could suppress the free carrier absorption (if $V_{\rm dc} \ (!_{\rm B} \ + \ !_1))$ V $_{\rm dc} \ (!_{\rm B} \ + \ !_1))$ or even make its value negative (if $V_{\rm dc} \ (!_{\rm B} \ + \ !_1))$.

On the other hand, it is easy to see that in the quasistatic lim it, $!_1$ 1, the nite di erence in Eq.60 goes to the derivative $@V_{dc}=@E_{dc}$, which determ ines the slope of dependence of V_{dc} on dc bias at the working point E_{dc} . The sign of this derivative controls electric stability against spatial perturbations of charge density [12, 17]: For negative slope $@V_{dc}=@E_{dc} < 0$ destructive space-charge instability arises inside SL. In contrast, $@V_{dc}=@E_{dc} > 0$ is the necessary condition for absence of the electric dom ains in moderately doped SLs [12].

For general case $!_1$ & 1 our numerical analysis showed that the sign of nite di erence (d) is almost always same as the sign of the derivative $@V_{dc}=@E_{dc}$, if SL is unbiased ($E_{dc} = 0$) or only weakly biased. Therefore $A_{inc} > 0$ guarantees electric stability. The total absorption $A = A_{coh} + A_{inc}$ still can be negative in conditions of electric stability if j ___________________ =4 and jA_{coh} $\Rightarrow A_{inc}$. In the case of unbiased SL (Fig. 1), such situation is illustrated in Figs 2,3. Fig. 2 shows the regions of negative absorption (A < 0) at even harm onics together with the regions of NDC ($@V_{dc}=@E_{dc} < 0$) in $!E_0$ plane. Here the phase is chosen to be optim al (Eq. 3). The values of E_0 and ! resulting in electric instability (red areas in



FIG. 2: (color online) Ampli cation at even harmonics in unbiased superlattice for $= _{opt}$. Regions above the marked curves correspond to gain at $!_1 = :2!$;4!;6!. Dark (red online) areas correspond to electric instability.



FIG. 3: (color online) M agnitude of negative absorption at even harm onics (m arked curves) as a function of the pump frequency ! for the xed pump amplitude E $_0$ = 5:1 and = $_{opt}$. D ark (red online) segments indicate intervals of NDC.

Fig.2) are close to the lines of B essel roots $J_0() = 0$. It can be explained noticing that for E_{dc} ! 0 transition to NDC is accompanied by absolute negative conductivity (ANC) [12]. However, as can be derived from Eq.7 in the limit E_{dc} ! 0, ANC arises only for $J_0()$ ' 0 [11]. In portantly, the regions of gain and areas of instability overlap only in limited ranges of the pump amplitudes and frequencies. Moreover, the magnitude of dom ain less gain is signing cantieven at room temperature (Fig.3). To estimate gain in units cm⁻¹ [15] we used the form ula $= _0 (A=E_1)$ with $_0 = 8 \text{ eN } V_p = (E_cn_rc)$ and the following typical semiconductor SL parameters: a = 6 nm, = 60 meV, electron density N = 10^{16} cm^{-3} , = 200



FIG.4: (color online) Ampli cation with a low threshold at $!_1 = !=2$ in biased superlattice for $E_{dc} = 1$ and $= _{opt}$. M arked region between curves corresponds to gain, while dark (red online) area corresponds to electric instability. Inset: M agnitude of negative absorption as function of the pump amplitude E_0 for ! = 0.25.

fs, refractive index $n_{\rm r}$ = ${}^{\rm p} \, \overline{13}$ (G aA s) and T = 300 K .

E ven harm onics of the pum p satisfy the param etric resonance condition $!_{"}^{even} = 2 = !_1$. For unbiased case only this scheme provides amplication which is una ected by generated harm onics. On the other hand, for $E_{dc} \in 0$ subharm onics of the pump $(!_1 = : !=2;3!=2;:::)$ satis fy another parametric resonance condition $!_{a}^{odd}=2$ = $!_{1}$. W e found that regions of gain at di erent half-harm on ics and areas of electric instability (NDC) have no overlapping for many values of E $_{\rm 0}$ and ! . Fig.4 illustrates this for ampli cation at $!_1 = ! = 2$ and $E_{dc} = 1$. Here threshold is very low while gain is still signi cant even 0:5 (Fig.4, inset). We explain it analyzing the at E o behavior of both A_{coh} and A_{inc} for small E_0 . First, for $!_1 = ! = 1 = 2$ relatively large rst harmonics (s = 1) of the quantum reactive parameters contribute to $A_{coh} < 0$ (Eq. 4). Second, the tangent to the curve describing a dependence of V_{dc} on E_{dc} (Eq. 7) has a small positive slope at the working point $E_{dc} = 1$. Following Eq. 6 it results in a rather sm all $A_{inc} > 0$. Therefore the total gain A < 0 is not sm all.

In this Letter, we focused on the phase-sensitive degenerate parametric amplication of THz elds in SLs. Our theory can be directly extended to describe nondegenerate phase-insensitive amplication. Here, at least for the case of unbiased SL, regions of NDC in $! E_0$ plane are still located only near Bessel roots lines (cf. Fig. 2). Therefore, by a proper choice of amplitude and frequency of the pump it is also possible to reach electrically stable ampli-

cation of weak signal $(!_1)$ and idler $(!_2)$ elds satisfying the parametric resonance condition $!_{\mu}^{\text{even}} = !_1 + !_2$.

The parametric e ects in a nonparabolic energy band should exist not only in sem iconductor SLs but also in other articial periodic structures, including periodic waveguide arrays [18] and m icrocavity SLs [19] for light, phononic m icrocavity arrays [20], carbon nanotube SLs in perpendicular electric eld 21], and dissipative optical lattices for ultracold atom s [22]. These SLs were specially suggested and designed to manifest e ects of B loch oscillations [19, 20, 21, 22] or ac eld [8, 21] in a single band and therefore potentially can be used to observe the param etric am pli cation.

In sum m ary, we described physical mechanisms for the parametric resonance and resulting high-frequency am – pli cation in an energy band. The parametric ampli cation of a weak signal is possible without negative di erential conductance. Parametric e ects due to Bragg re-

ections in ac-driven lattices are no less important than manifestations of B loch oscillations in the case of a pure dc bias.

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